/ Descriptions

TO-220F PNP Silicon PNP transistor in a TO-220F Plastic Package.

/ Features

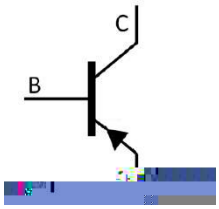
, KTC4369

Good linearity of h_{FE}, complementary to KTC4369.

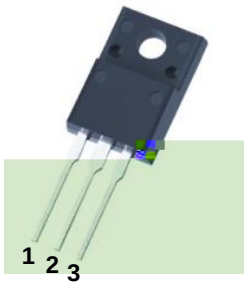
/ Applications

General purpose amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	70 140	120 240

/ Absolute Maximum Ratings(Ta=25)

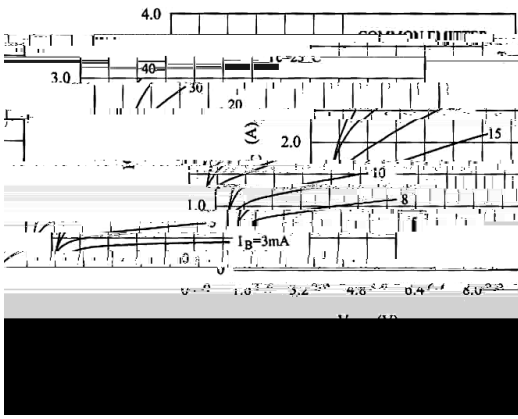
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-3.0	A
Base Current	I_B	-0.3	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	P_C(Tc=25)	15	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

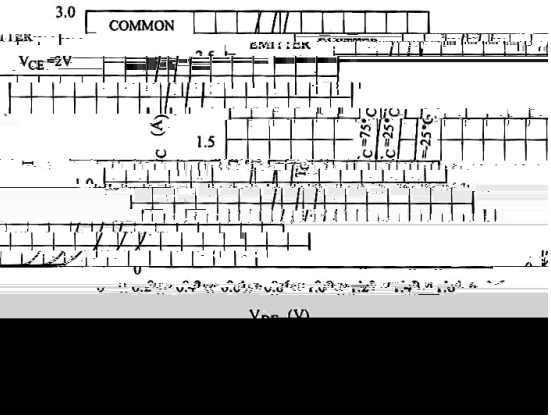
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-10mA I_B=0	-30			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-20V I_E=0			-1.0	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-1.0	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-2.0V I_C=-0.5A	70		240	
	$h_{FE(2)}$	V_{CE}=-2.0V I_C=-2.5A	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-2.0A I_B=-0.2A		-0.3	-0.8	V
Collector to Emitter Voltage	V_{BE}	V_{CE}=-2.0V I_C=-0.5A		-0.75	-1.0	V
Transition Frequency	f_T	V_{CE}=-2.0V I_C=-0.5A		100		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V I_E=0 f=1.0MHz		40		pF

/ Electrical Characteristic Curve

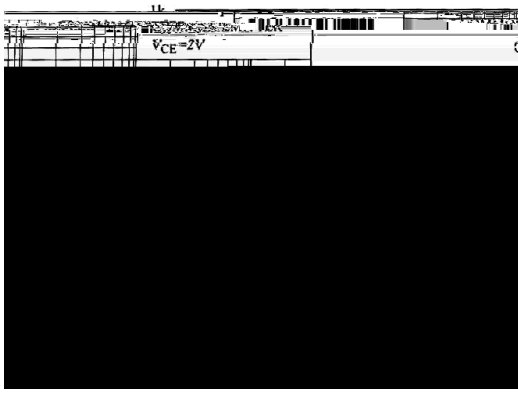
I_C - V_{CE}



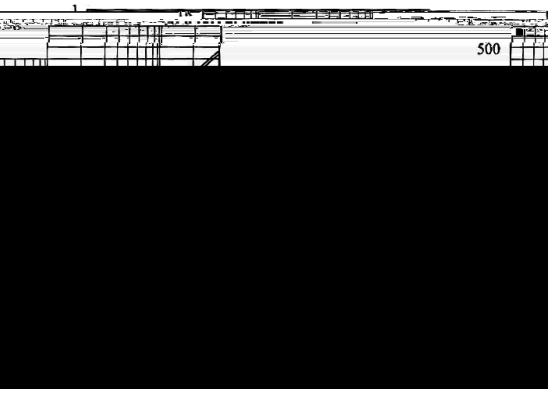
I_C - V_{BE}

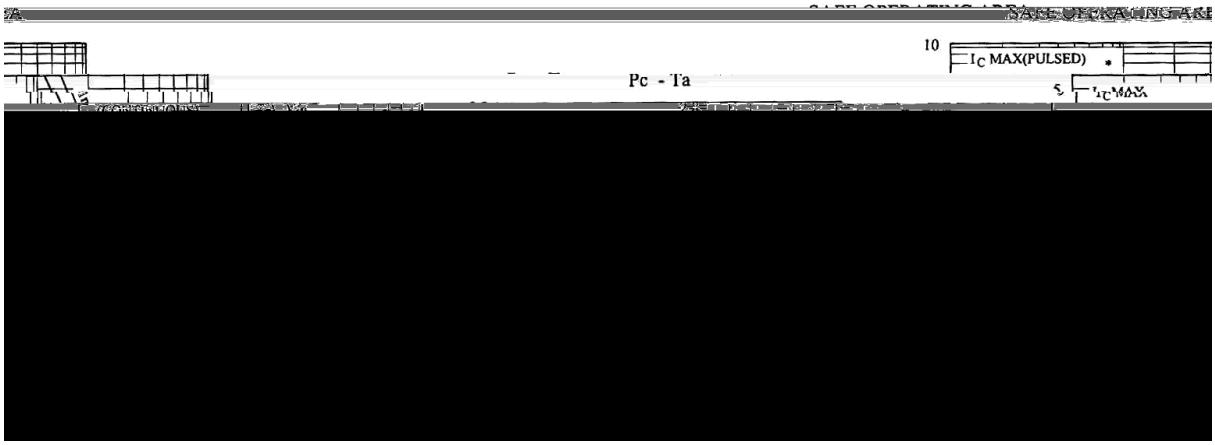


h_{FE} - I_C



$V_{CE(sat)}$ - I_C



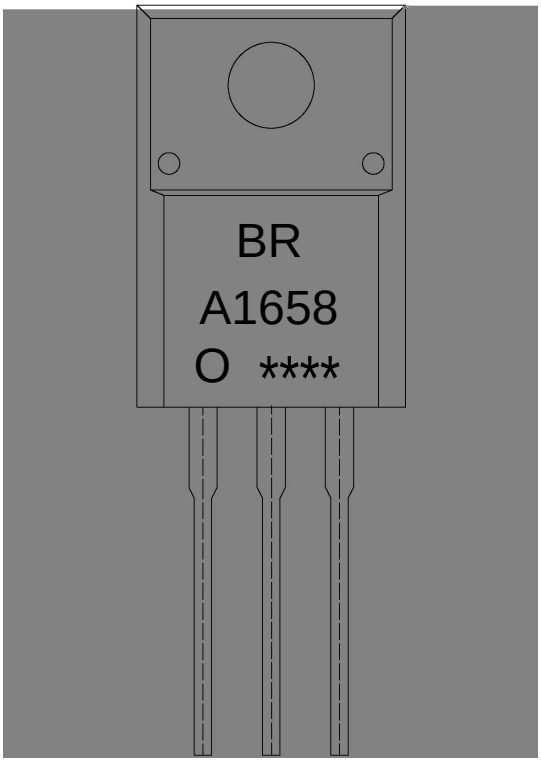


Pc - Ta

/ Package Dimensions



/ Marking Instructions



BR

A1658

O: h_{FE}

****

Note:

BR: Company Code.

A1658: Product Type.

O: h_{FE} Classifications Symbol.

****: Lot No. Code, code change with Lot No.